RECEIVED
CENTRAL FAX CENTER
OCT 26 2006



**IN THE CLAIMS:**

1. (Currently Amended) A method for manufacturing a semiconductor device, comprising the steps of:

forming a laminate comprising a first conductive layer and a second conductive layer over a semiconductor layer with a gate insulating film interposed therebetween over a substrate;

forming a mask pattern over the laminate;

etching the second conductive layer and the first conductive layer while recessing the mask pattern over the laminate with the use of plasma to which $SF_6$ is added; and

forming a lightly doped drain region in a region of the semiconductor [[film]] layer.

2. (Original) The method according to claim 1, wherein the first conductive layer is tantalum nitride, and the second conductive layer is titanium or one of an alloy and a compound including titanium as its main component.

3. (Original) The method according to claim 1, wherein the method further comprising a step of selectively etching the second conductive layer after the etching step in accordance with the mask pattern left over the laminate.

4. (Original) The method according to claim 1, wherein $CF_4$, $SF_6$, $Cl_2$, and $O_2$ is used as etching gas in the etching step.

5. (Original) The method according to claim 1, wherein ECR (Electron Cyclotron Resonance) or ICP (Inductively Coupled Plasma) is used for the etching step.

6. (Original) The method according to claim 1, wherein a negative bias voltage is applied to the substrate side during the etching step.

7. (Currently Amended) A method for manufacturing a semiconductor device, comprising the steps of:

laminating a first conductive layer, a second conductive layer, and a third conductive layer sequentially over a semiconductor layer with a gate insulating film interposed therebetween to form a laminate over a substrate;

forming a mask pattern over the laminate;

etching the third conductive layer, the second conductive layer and the first conductive layer while recessing the mask pattern over the laminate with the use of plasma to which $SF_6$ is added; and

forming a lightly doped drain region in a region of the semiconductor [[film]] layer.

8. (Original) The method according to claim 7, wherein the first conductive layer is tantalum nitride, the second conductive layer is titanium or one of an alloy and a compound including titanium as its main component, and the third conductive layer is titanium nitride.

9. (Original) The method according to claim 7, wherein the method further comprising a step of selectively etching the third conductive layer and the second conductive layer after the etching step in accordance with the mask pattern left over the laminate.

10. (Original) The method according to claim 7, wherein $CF_4$, $SF_6$, $Cl_2$, and $O_2$ is used as etching gas in the etching step.

11. (Original) The method according to claim 7, wherein ECR (Electron Cyclotron Resonance) or ICP (Inductively Coupled Plasma) is used for the etching step.

12. (Original) The method according to claim 7, wherein a negative bias voltage is applied to the substrate side during the etching step.